

In the Claims:

Kindly amend claims 389-409 as follows:

389. (Currently Amended) Wafer boat preform comprising boat fabrication material selected from a group consisting of silicon, silicon compound comprising at least one silicon atom, silicon and germanium, $\text{Si}_x\text{Ge}_{1-x}$ solid solution, silicon and Silicon Carbide $\text{Si}_x(\text{SiC})_{1-x}$, Silicon and silicon dioxide $\text{Si}_x(\text{SiO}_2)_{1-x}$, silicon and any ceramic, silicon and any oxide $\text{Si}_x(\text{Oxide})_{1-x}$, silicon and any metal $\text{Si}_x\text{M}_{1-x}$, Silicon and any alloy $\text{Si}_x\text{A}_{1-x}$, any combination between themselves, or made from composite material, wherein $0 \leq x \leq 1$.

390. (Previously Presented) The wafer boat preform of claim 389, wherein the boat is made by pressing the boat fabrication material within a die having desired shape and form, sintering, cooling it down at a desired cool-down regime, and machining it to a desired tolerance.

391. (Previously Presented) The wafer boat preform of claim 390, wherein the boat fabrication material is powder mixed with organic and/or inorganic compounds for shaping purposes.

392. (Previously Presented) The wafer boat preform of claim 389, wherein the melting or sintering is preceded by one or more steps of purging and purification.

393. (Currently Amended) A process for fabrication of wafer boat preforms, comprising providing a boat fabrication material selected from a group consisting of silicon, silicon compound comprising at least one silicon atom, silicon and germanium, $\text{Si}_x\text{Ge}_{1-x}$ solid solution, silicon and silicon carbide $\text{Si}_x(\text{SiC})_{1-x}$, Silicon and silicon dioxide $\text{Si}_x(\text{SiO}_2)_{1-x}$, silicon and any ceramic, silicon and any oxide $\text{Si}_x(\text{Oxide})_{1-x}$, silicon and any metal $\text{Si}_x\text{M}_{1-x}$, Silicon and

any alloy $\text{Si}_x\text{A}_{1-x}$, any combination between themselves, or made from composite material, wherein $0 \leq x \leq 1$.

394. (Previously Presented) The process of claim 393, further comprising extruding the fabrication material within a die having desired shape and form, sintering, cooling it down at a desired cool-down regime, and machining it to a desired tolerance.

395. (Previously Presented) The process of claim 394, wherein the boat fabrication material is powder.

396. (Previously Presented) The process of claim 395, wherein the boat fabrication material is powder mixed with organic or inorganic materials.

397. (Previously Presented) The process of claim 394, wherein pressing is done under reduced or high pressure of inert or reactive gas.

398. (Previously Presented) The process of claim 397, wherein the reactive gas is a mixture between atomic or charged molecular state gas such as plasma gas and a neutral inert or reactive gas.

399. (Currently Amended) Process for fabrication of a member having shape of tube, plate, rod or any other shape or form consisting of providing a material selected from a group consisting of silicon, silicon compound comprising at least one silicon atom, silicon and germanium, $\text{Si}_x\text{Ge}_{1-x}$ solid solution, silicon and silicon carbide $\text{Si}_x(\text{SiC})_{1-x}$, silicon and silicon dioxide $\text{Si}_x(\text{SiO}_2)_{1-x}$, silicon and any ceramic, silicon and any oxide $\text{Si}_x(\text{Oxide})_{1-x}$, silicon and any metal $\text{Si}_x\text{M}_{1-x}$, Silicon and any alloy $\text{Si}_x\text{A}_{1-x}$, any combination between themselves, or made from composite material, wherein $0 \leq x \leq 1$.

400. (Previously Presented) The process of claim 399, further comprising heating and melting or sintering the material made with a mold having desired shape and form, or transferring the material to the mold, solidifying it, cooling it down at a desired cool-down regime, removing the mold, machining it to the desired tolerance, and sintering again.

401. (Previously Presented) The process of claim 400, wherein the material is powder mixed with organic or inorganic materials.

402. (Previously Presented) The process of claim 400, wherein the melting is done in a vacuum chamber.

403. (Previously Presented) The process of claim 400, wherein the melting or sintering is done under reduced or high pressure of inert or reactive gas.

404. (Previously Presented) The process of claim 400, wherein the melting or sintering is preceded by one or more steps of purging and purification.

405. (Previously Presented) The process of claim 399, further comprising fabricating wafer boat members having shape of tube, plate, rod or any other shape.

406. (Previously Presented) The process of claim 405, further comprising cutting the member or solidified boat in two along medial lines, forming openings in cylindrical walls, coating and fusing depositing material on top of base material.

407. (Previously Presented) The process of claim 405, further comprising forming slots in inward and/or outward ribs or extensions, forming ends of the boats having complementary steps to connect the boats end-to-end in an axial stack or row.

408. (Previously Presented) The process of claim 407, further comprising forming a chamber liner and applying to a process chamber, forming a chemical vapor deposition (CVD) station, halving formed tubes lengthwise, cutting windows, inward ribs or extensions in the tubes, or the inner walls are slotted, forming a vertical boat, and in parallel steps cutting windows, plotting the boat and forming a horizontal boat.

409. (Previously Presented) The process of manufacturing a electronic chip comprising the steps of:

(a) making a complete chamber or wafer processing member of the chamber for processing at least one wafer;

(b) making the complete chamber or wafer processing member using fabrication material selected from a group comprising of silicon, silicon compound comprising at least one silicon atom, silicon and germanium, $\text{Si}_x\text{Ge}_{1-x}$ solid solution, silicon and Silicon Carbide $\text{Si}_x(\text{SiC})_{1-x}$, Silicon and silicon dioxide $\text{Si}_x(\text{SiO}_2)_{1-x}$, silicon and any ceramic, silicon and any oxide $\text{Si}_x(\text{Oxide})_{1-x}$, silicon and any metal $\text{Si}_x\text{M}_{1-x}$, Silicon and any alloy $\text{Si}_x\text{A}_{1-x}$, any combination between themselves, or made from composite material, wherein $0 < x < 1$ for holding the wafer;

(c) making the complete chamber or wafer processing part using process comprising of

1. Forging,
2. Extrusion,
3. Plasma deposition;
4. Hot substrate powder deposition
5. Powder deposition
6. CVD deposition
7. Slurry spray
8. Slurry processing
9. Casting;
10. Gelcasting
11. Directional solidification,
12. Crystal growth
13. Powder processing
14. Any process combination

(d) placing the wafer in the chamber and on the wafer processing member at least for a period of time that the wafer is in the chamber;

(e) processing the wafer in the chamber;

- (f) removing the wafer from the chamber; and
- (g) further processing the wafer to make at least one electronic chip comprising one or more electronic devices.
- (h) further processing the wafer to make at least one computer chip comprising one or more electronic devices.